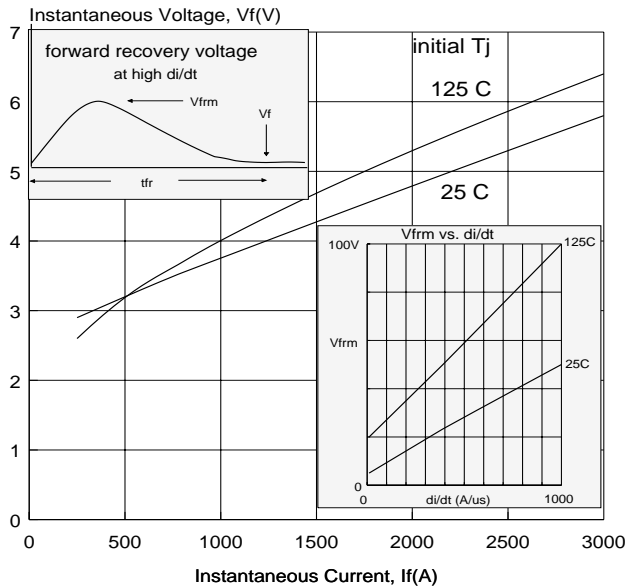


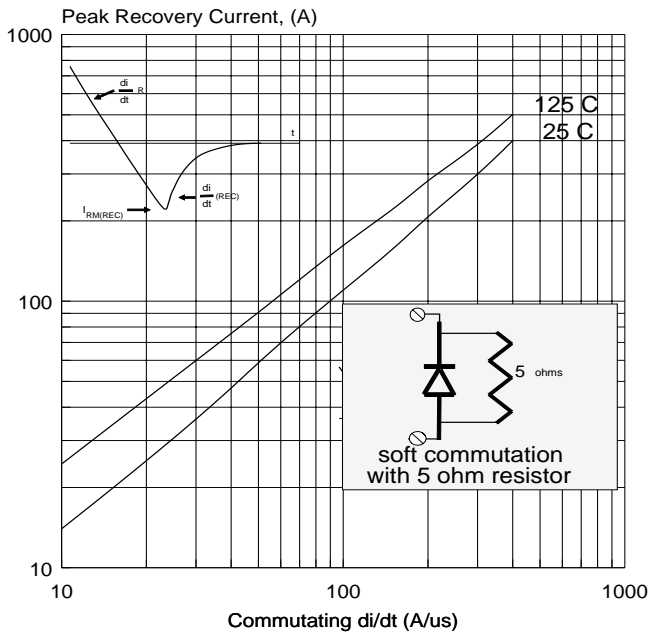
The SDD63HK fast recovery diode is designed for use in complex snubber circuits commonly used for gate turn-off thyristors, GTO's, for which the low forward recovery voltage developed by the diode at extremely high di/dt is important in order to achieve full turn-off capability. It is manufactured by the proven multi-diffusion process and is supplied in a disc-type package, ready to mount using commercially available heat dissipators and clamping hardware.

Forward EI Characteristic - typical
8 ms pulse



T63 5/11/90

Peak Recovery Current
typical diode



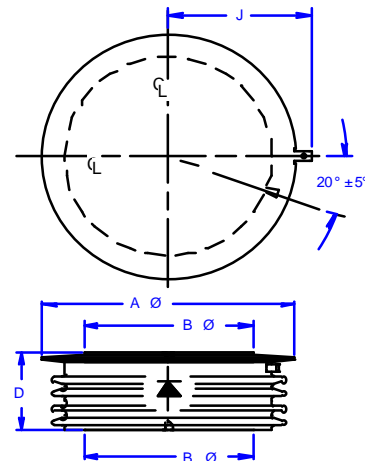
T63 5/10/90

Principal Ratings and Characteristics

Repetitive peak reverse voltage	V_{RRM}	$T_J = -40$ to 125°C	up to 4500	V
Peak forward recovery voltage	V_{FRM}	@1000A/us	50	V
Forward recovery time	t_{fr}	@1000A/us	2	μs
Forward turn-on time	t_{on}	$I_F = 1000\text{A}$	4	μs
Peak forward drop	V_f	@ $I_F = 1000\text{A}$	5	V

Note: All values are maximum at 25°C unless noted.

MECHANICAL OUTLINE



AF = 2.30 in (58.0 mm)
BF = 1.35 in (34.3 mm)
D = 1.04 in (26.4 mm)

ALLOWABLE RANGE CLAMPING FORCE
450 - 3500 lb / 2 - 16 kN